

Silicon PNP Power Transistors

2SB1033

DESCRIPTION

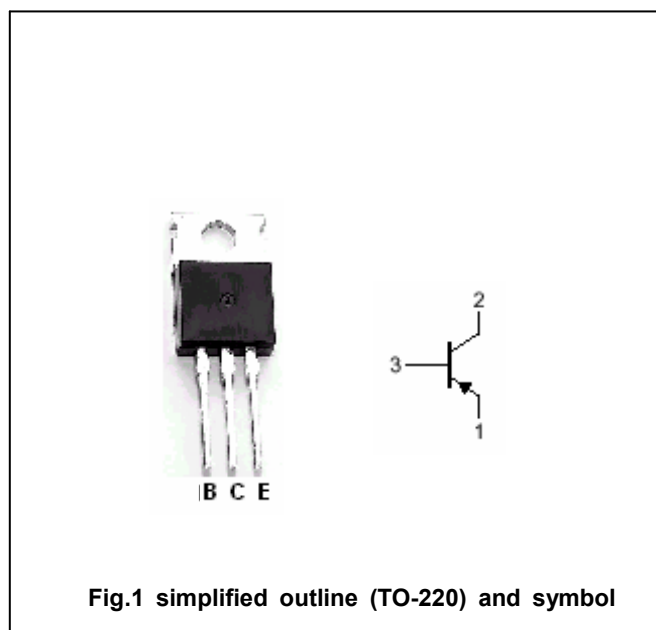
- With TO-220 package
- Complement to type 2SD1437

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

**Absolute maximum ratings(Ta=25℃)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-3	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	40	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Base-emitter breakdown voltage	$I_C=-25mA, I_B=0$	-60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-1mA, I_E=0$	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1mA, I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-2A; I_B=-0.2A$			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-2A; I_B=-0.2A$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-60V; I_E=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-10	μA
h_{FE}	DC current gain	$I_C=-0.5A; V_{CE}=-5V$	60		320	
f_T	Transition frequency	$I_C=-0.5A; V_{CE}=-5V$		12		MHz
C_{ob}	Output capacitance	$I_E=0; V_{CB}=-10V; f=1MHz$		100		pF

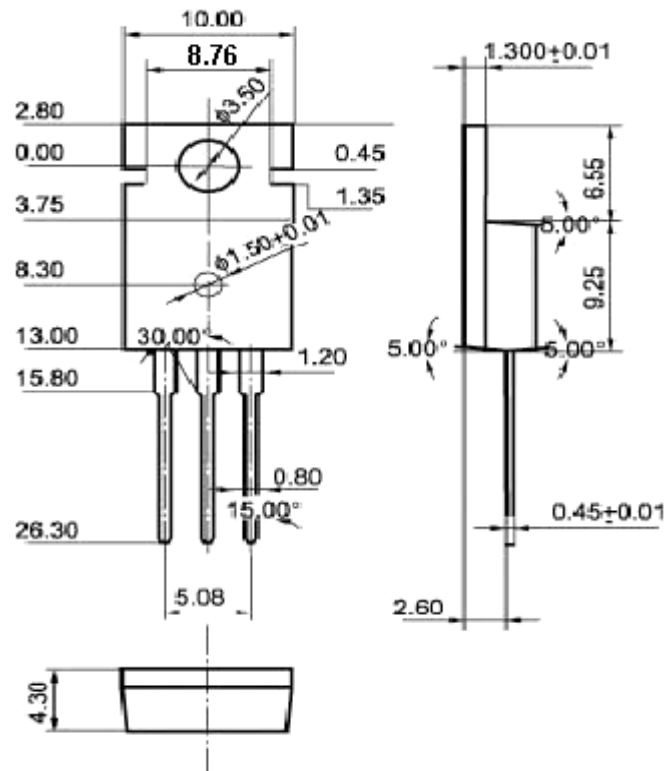
◆ h_{FE} Classifications

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)